ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D=12V R_L=33Ω	- -	MAX.	5	mA
				10	
V_{GT}		ALL	MAX.	1	V
V_{GD}	V_D=V_{DRM} T_j=125 R_L=3.3kΩ	ALL	MIN.	0.2	V
I_L	I_G=1.2I_{GT}	- -	MAX.	10	mA
				20	
I_H	I_T=100mA		MAX.	7	mA
dV/dt	V_D=540V Gate Open T_j=110		MIN.	100	V/μs
(dV/dt)c	(dI/dt)c=1.8A/ms, T_j=110		MIN.	2.5	V/μs
t_{on}	I_G=20mA I_A=200mA I_R=20mA T_j=25		TYP.	2.5	μs
t_{off}				25	

STATIC CHARACTERISTICS

Symbol	Parameter		Value (MAX.)	Unit
V_{TM}	I_{TM}=5A t_p=380μs	T_j=25	1.55	V
V_{TO}	Threshold voltage	T_j=125	0.92	V
R_D	Dynamic resistance	T_j=125	107	mΩ
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25	5	μA
I_{RRM}		T_j=125	0.35	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.5	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

ORDERING INFORMATION

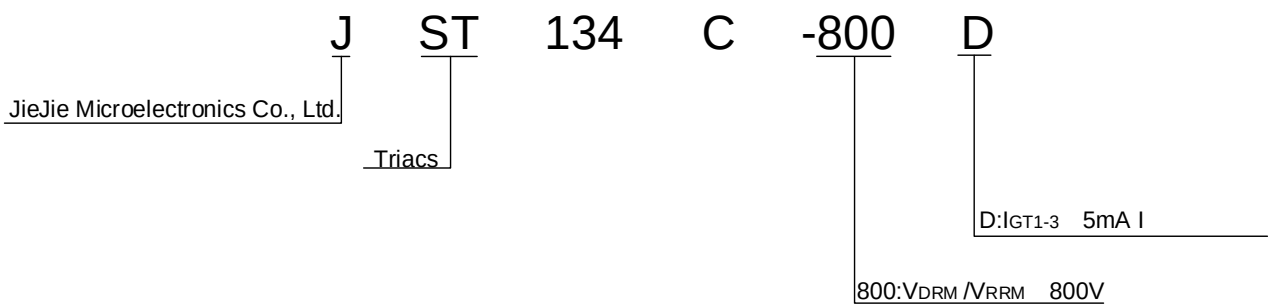


FIG.1: Maximum power dissipation versus RMS on-state current

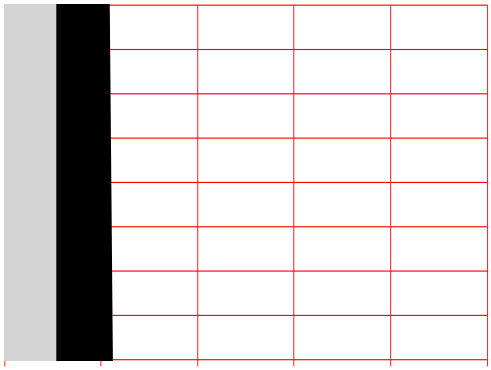
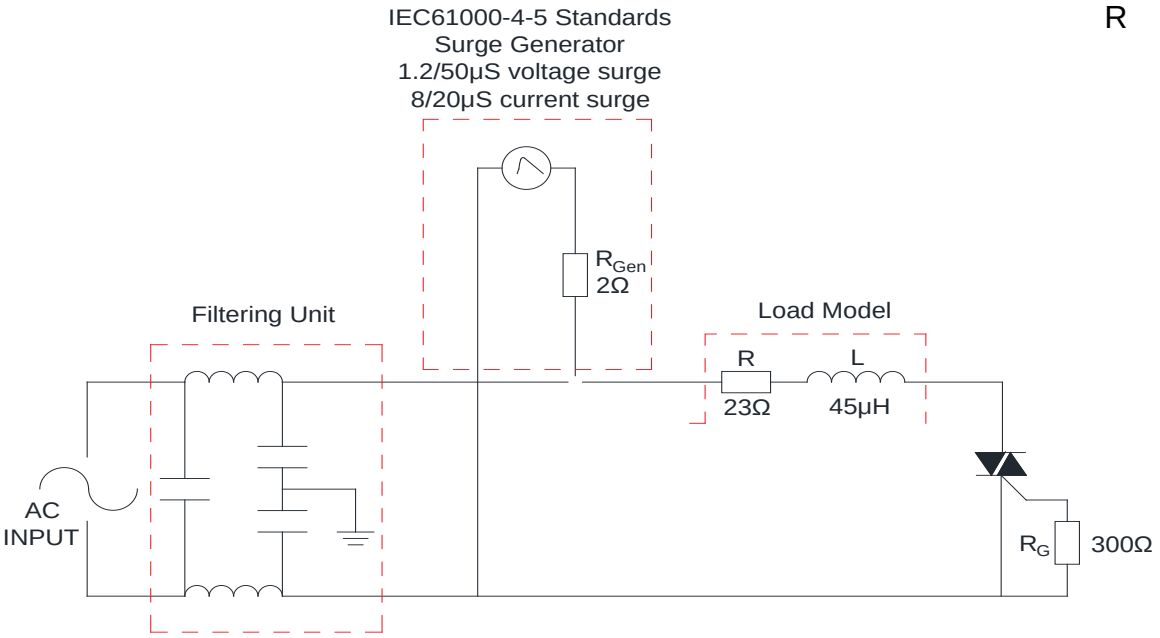


FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



PACKAGE MECHANICAL DATA



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this d4 ( )]TJ -18Tu-18Tu- (uc)1 i6 (m5> n)10 (n5.l)12 (n(s)4 ( )(i)6.1 be)10
of e nn5.e,(n)10 ap6 (i)1 (m)- e (c)4 ((n t)2 (hi (o)10ha)-8 (e)102 -1.3hen an a)]TJ -sse (n t)2 (hi)6 (
JiiyhipesTw 0.55 2 -1.3 Td [(o)10 ii